

S/N 09/945,535

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: David S. Blum

Serial No.: 09/945,535

Group Art Unit: 2813

Filed: August 30, 2001

Docket: 1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO₂

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS RCE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :09/945,535

Filing Date: August 30, 2001

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2

Page 2

Dkt: 1303.026US1

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 2/09/05

By David Suhl
David Suhl
Reg. No. 43,169

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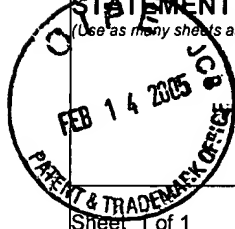
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Complete if Known

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|----------------------|-----------------|
| Application Number | 09/945,535 |
| Filing Date | August 30, 2001 |
| First Named Inventor | Ahn, Kie |
| Group Art Unit | 2813 |
| Examiner Name | Blum, David |

Sheet 1 of 1

Attorney Docket No: 1303.026US1

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Serial No.: 09/945,535

Group Art Unit: 2813

Filed: August 30, 2001

Docket: 1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZRO2

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop RCE
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Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

| <u>Serial/Patent No.</u> | <u>Filing Date</u> | <u>Attorney Docket</u> | <u>Title</u> |
|--------------------------|--------------------|------------------------|---|
| 11/036296 | January 14, 2005 | 1303.030US2 | LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS |
| 10/930138 | August 31, 2004 | 1303.044US2 | EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELECTRICS |
| 10/930184 | August 31, 2004 | 1303.021US2 | CRYSTALLINE OR AMORPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND GD2O3 |
| 10/930516 | August 31, 2004 | 1303.078US2 | ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS |
| 10/931341 | August 31, 2004 | 1303.082US2 | ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiH4 |
| 10/930431 | August 31, 2004 | 1303.056US2 | ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS |
| 10/931365 | August 31, 2004 | 1303.059US2 | Pr2O3-BASED La-oxide GATE DIELECTRICS |
| 10/931364 | August 31, 2004 | 1303.069US2 | LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION |

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 09/945,535

Filing Date: August 30, 2001

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO₂

Page 2

Dkt: 1303.026US1

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|-----------|--------------------|-------------|--|
| 10/931343 | August 31, 2004 | 1303.101US2 | LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS |
| 10/931340 | August 31, 2004 | 1303.107US2 | LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS |
| 10/931356 | August 31, 2004 | 1303.026US2 | HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO ₂ |
| 11/031289 | January 7, 2005 | 1303.069US3 | LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA OXIDATION |

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

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Date 2/09/05 By David Suhl
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Name

Kacia Lee
Signature

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number 09/945535
Filing Date August 30, 2001
First Named Inventor Ahn, Kie
Group Art Unit 2813
Examiner Name Blum, David

Attorney Docket No: 1303.026US1

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| | Group Art Unit | 2813 |
| | Examiner Name | Blum, David |
| Sheet 2 of 3 | | Attorney Docket No: 1303.026US1 |

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Substitute Disclosure Statement Form (PTO-1449)

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| First Named Inventor | Ahn, Kie |
| Group Art Unit | 2813 |
| Examiner Name | Blum, David |

Sheet 3 of 3

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| Examiner Name | Blum, David |

Sheet 1 of 8

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Sheet 2 of 8

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